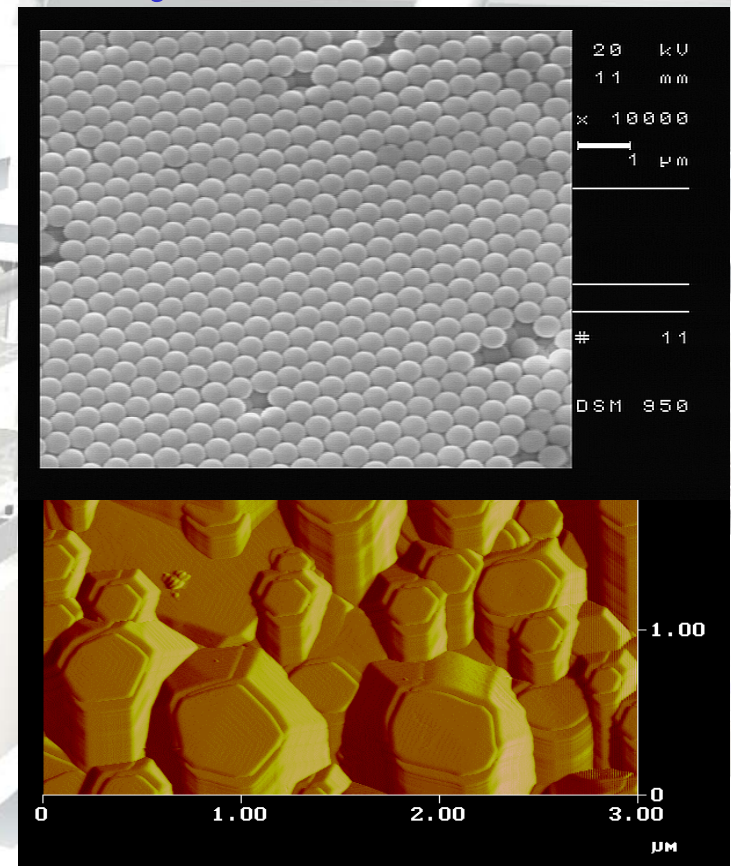




## Optoelectronics Laboratory

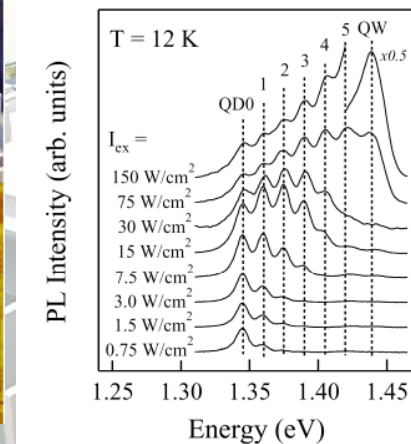
- **Employees: 19 (13 graduate students)**
  - professor Harri Lipsanen (nanotechnology),  
open: physics(optoelectronics) and photonics
- **Fields of research**
  - optoelectronics and integrated optics
  - compound semiconductor technology
  - nanotechnology, quantum structures
  - optical spectroscopy, x-ray diffraction
- **Teaching**
  - majors: photonics, nanotechnology,  
physics in electrical engineering
  - Master's Programme in Micro- and Nanotechnology





## Research in Optoelectronics

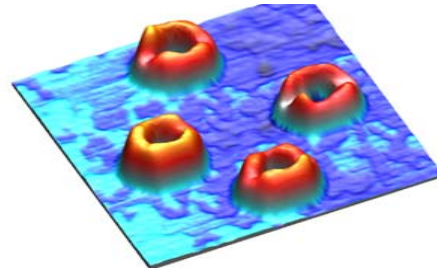
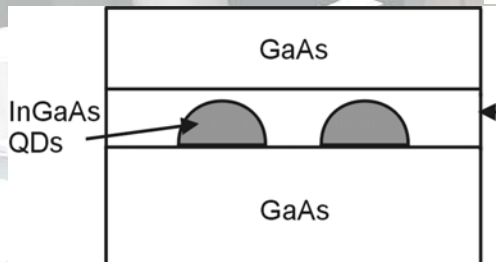
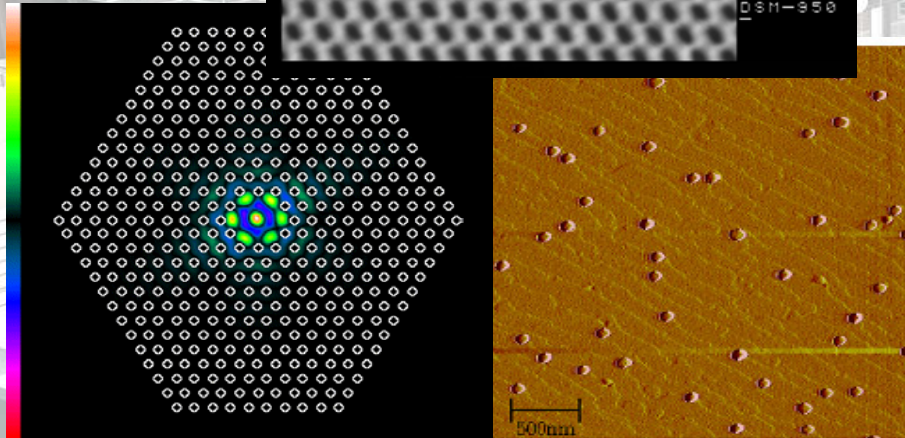
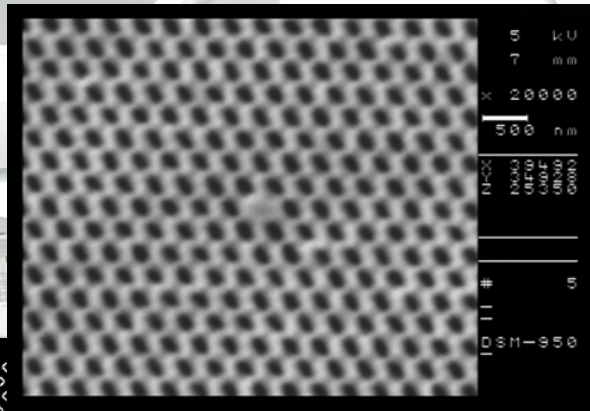
- Fabrication of compound semiconductor structures by metalorganic vapour phase epitaxy
- Materials characterisation by optical spectroscopy, x-ray diffraction and atomic force microscopy





## Advanced semiconductor structures

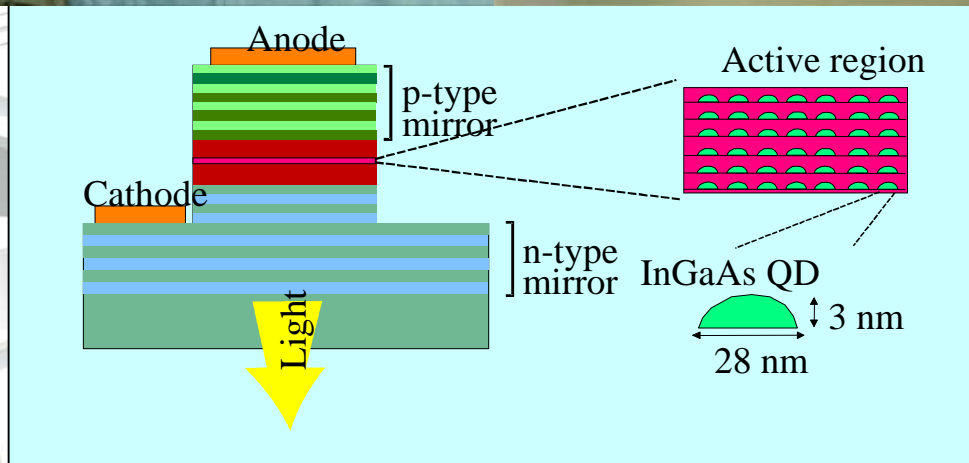
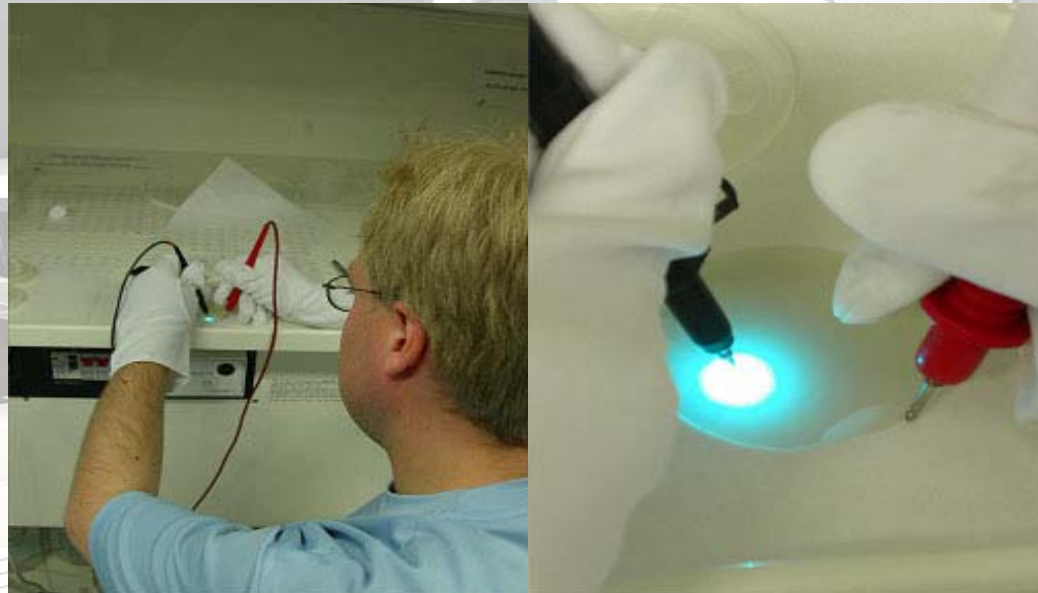
- Development of self-assembled quantum dot structures and photonic crystals for novel optoelectronic devices
- Gallium nitride technology for blue emitters and high-temperature electronics
- GaAs and InP technology for infrared applications





## Component processing

- **Devices:** diode lasers, LEDs, detectors, optical waveguides, microcavities and photonic crystals
- **Processes:** lithography, dry etching, metallisation, etc.
- **Materials:** GaAs-based, InP-based, GaN-based, InAs, GaSb, SOI





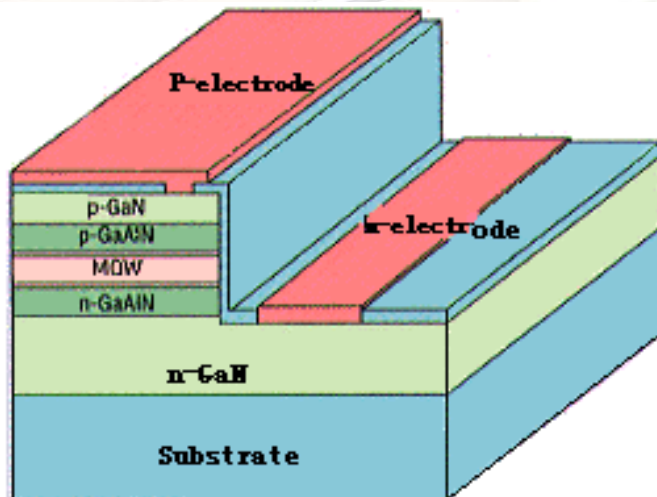
## Applications for the AlGaInN system

### • Optoelectronics

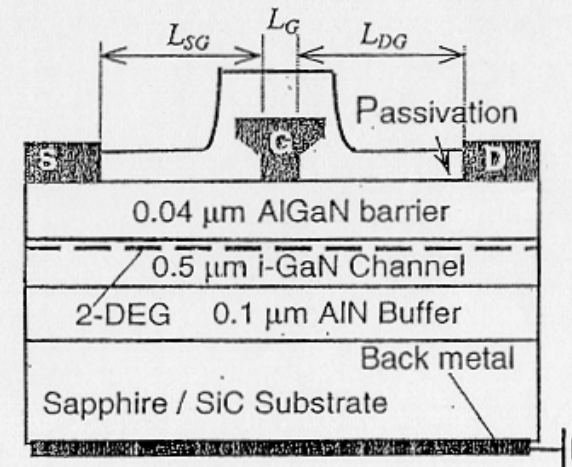
- ultrabright LEDs
- UV emitters and detectors
- blue/UV laser

### • Electronics

- power HEMTs



Device structure of a blue-light-emitting laser diode





### • Objectives

- 2-year target:**
- a) optically pumped lasing
  - b) electrically pulsed laser diode
- long term target:** cw blue laser

### • Materials research

- MOCVD growth of AlGaInN compounds on sapphire with reduced dislocation density
- improved GaN buffer layers on sapphire

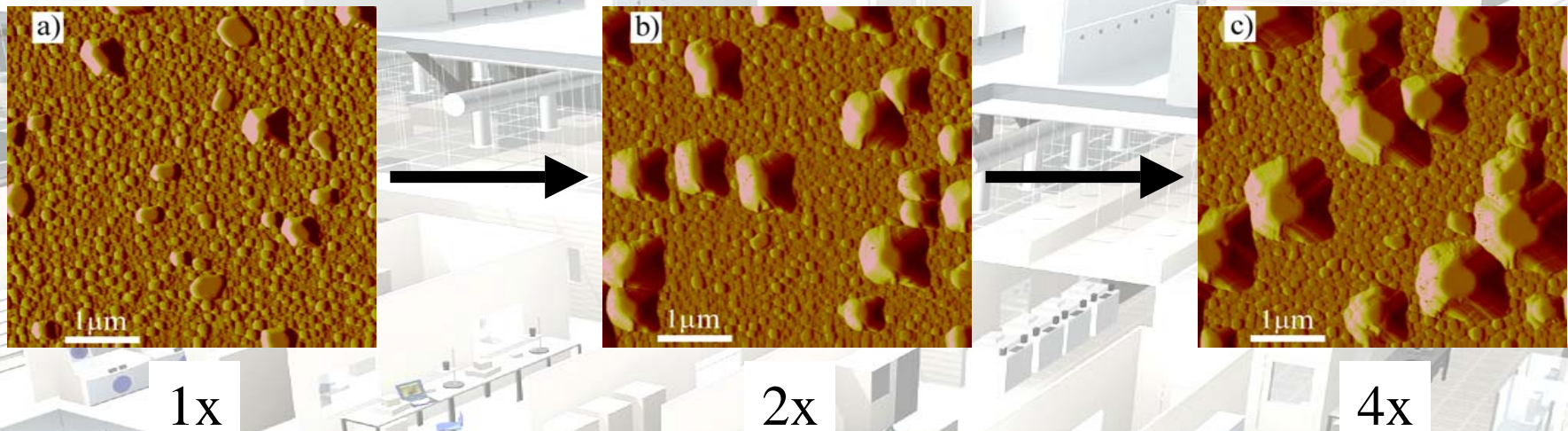
### • Device research

- high efficiency emitters by improvement in material quality, p-type doping
- development of GaN processing by ICP-RIE





## GaN nucleation on sapphire



- A cyclic method for nucleation layer optimization



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## MICRONOVA

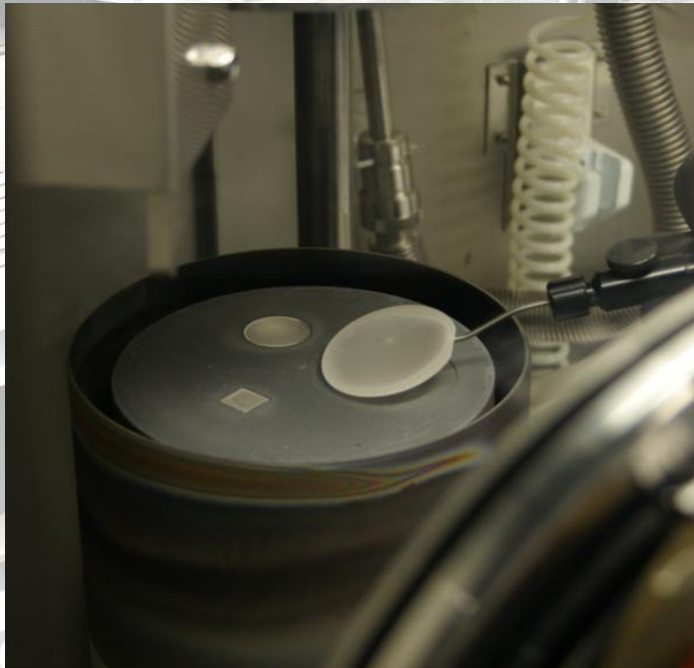
CENTRE FOR MICRO- AND NANOTECHNOLOGY

### EPITAXY:

MOCVD system for GaN epitaxy  
Thomas Swan 3x2" CCS reactor

### MATERIALS GROWN:

GaN, InN, AlGaIn, InGaIn



MOCVD system for III-V epitaxy: 1" horizontal reactor

### MATERIALS GROWN:

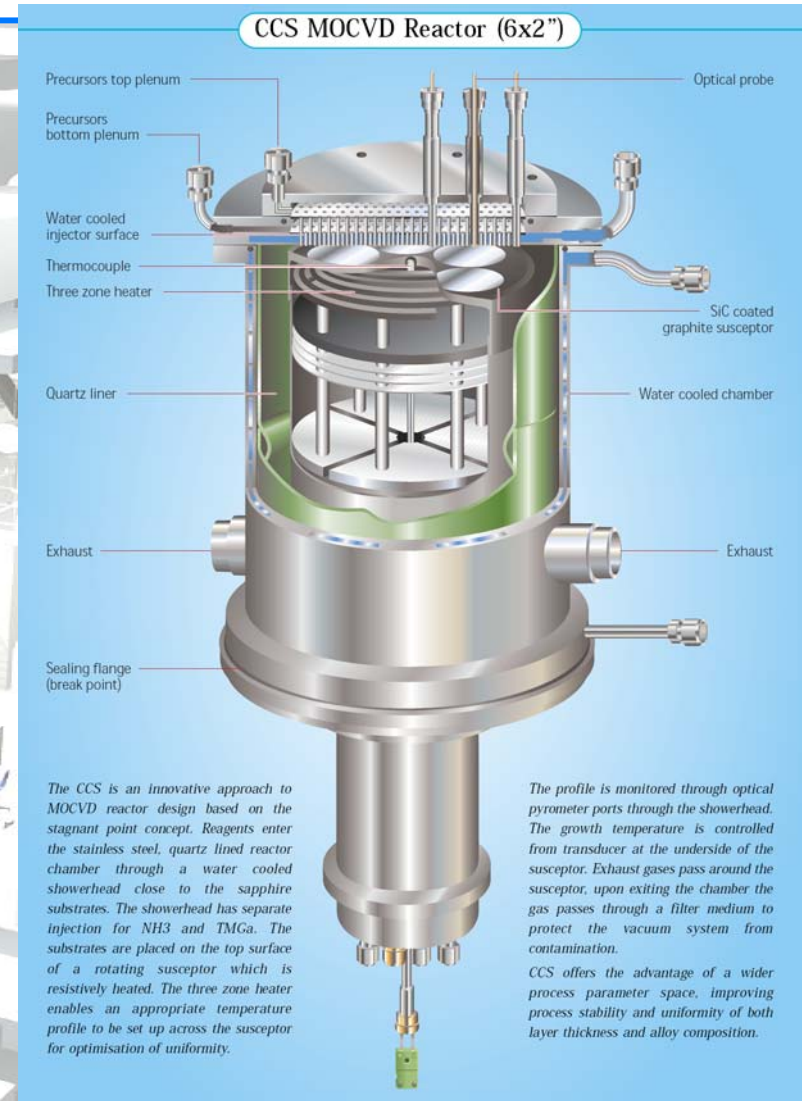
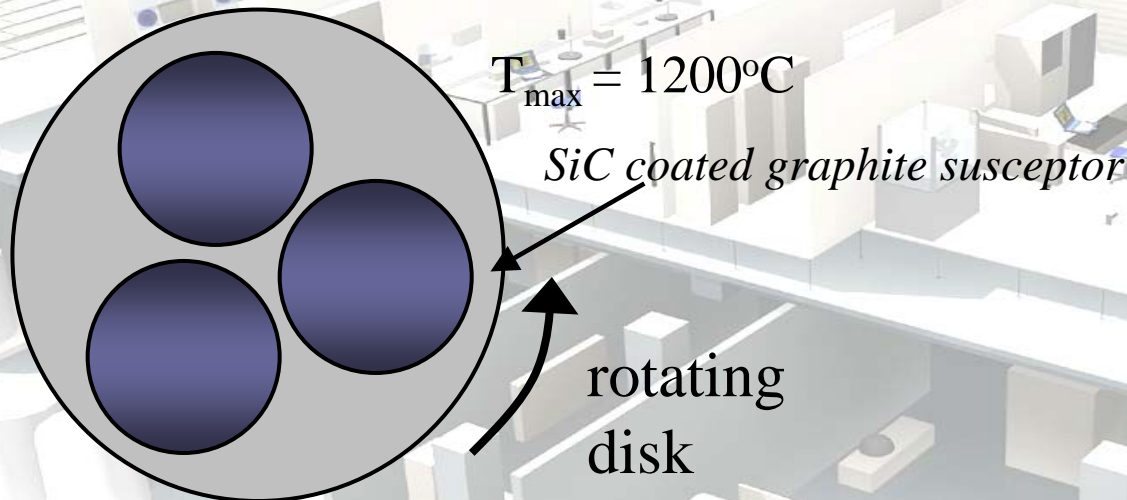
GaAs, InP, InAs, ...  
InGaAs, InGaP, GaAsN, ...  
GaInNAs, InGaAsP, ...





### Vertical 3 x 2" showerhead reactor

- growth of gallium nitride and other III-V's (arsenides and phosphides)
- real-time optical monitoring of growth (layer thickness, surface temperature...)
- excellent uniformity of thickness and alloy composition
- suitable for both research and production





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## MICRONOVA

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### PROCESSING:

ICP-RIE etching

Metallization

### CHARACTERIZATION:

Optical spectroscopy



X-ray diffraction



Atomic force microscopy

